





SOT-23 Formed SMD Package

BF820 BF822

SILICON EPITAXIAL TRANSISTORS

N-P-N transistors

Marking

BF820 = 1V

BF822 = 1X

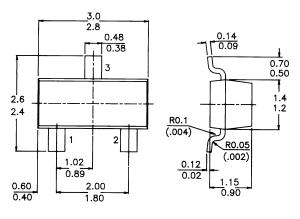
PACKAGE OUTLINE DETAILS
ALL DIMENSIONS IN mm

Pin configuration

1 = BASE 2 = EMITTER

3 = COLLECTOR





ABSOLUTE MAXIMUM RATINGS

			BF820		BF822
Collector-base voltage (open emitter)	V_{CB0}	max.	300		250 V
Collector-emitter voltage (open base)	V_{CE0}	max.	-		250 V
Collector-emitter voltage ($R_{BE} = 2.7 \text{ kW}$)	V_{CER}	max.	300		<i>V</i>
Collector current (peak value)	I_{CM}	max.		100	mA
Total power dissipation up to $T_{amb} = 25$ °C	P_{tot}	max.		<i>250</i>	mW
Junction temperature	T_j	max.		<i>150</i>	° C
D.C. current gain	· ·				
$I_C = 25 \text{ mA}; V_{CE} = 20 \text{ V}$	h_{FE}	>		<i>50</i>	
Feedback capacitance at $f = 1$ MHz					
$I_C = 0; \ V_{CE} = 30 \ V$	C_{re}	<		1,6	pF
Transition frequency at $f = 35$ MHz					
$I_C = 10 \text{mA}; \ V_{CE} = 10 \ V$	f_T	>		60	MHz

RATINGS (at $T_A = 25^{\circ}C$ unless otherwise specified) Limiting values

Limiting values					
			BF820	BF822	
Collector-base voltage (open emitter)	V_{CB0}	max.	300	250	\overline{V}
Collector-emitter voltage (open base)	V_{CE0}	max.	_	250	V
Collector-emitter voltage ($R_{BE} = 2.7 \text{ kW}$)	V_{CER}	max.	300	_	V
Emitter-base voltage (open collector)	V_{EB0}	max.		5	V
Collector current (d.c.)	I_C	max.		<i>50</i>	mA
Collector current (peak value)	I_{CM}	max.		100	mA
Total power dissipation					
$up to T_{amb} = 25 ^{\circ}C$	P_{tot}	max.		250	mW
Storage temperature	T_{stg}		-55	to +150	$^{\circ}$ C
Junction temperature	T_j	max.		150	° C
THERMAL RESISTANCE					
From junction to ambient	$R_{th\ j-a}$	$R_{th\ j-a}$		500	K/W
CHARACTERISTICS			BF820	BF82	22
$T_i = 25$ °C unless otherwise specified					_
Collector cut-off current					
$I_E = 0; \ V_{CB} = 200 \ V$	I_{CB0}	<	10	10	nΑ
Collector-emitter voltage					
R_{BE} = 2,7 kW; V_{CE} = 250 V	I_{CER}	<	<i>50</i>	50	nΑ
$R_{BE} = 2.7 \text{kW}$; $V_{CE} = 200 \text{V}$; $T_i = 150 \text{°C}$	I_{CER}	<	10	10	m A
Caturation voltage					

Notes

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/CD is believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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